

**TOSHIBA**

**TA8320F**

TENTATIVE TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MULTI CHIP

# TA8320F

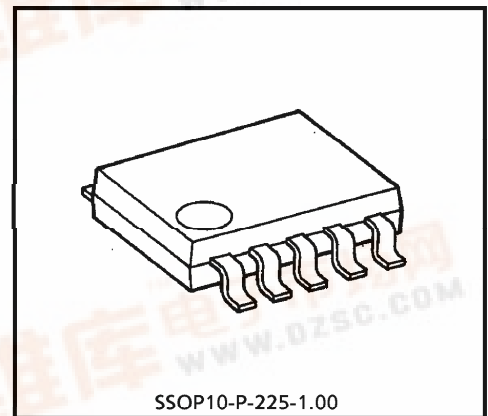
## LED DRIVER FOR CAMERA

TA8320F is Multi Chip IC incorporates 3 low saturation discrete transistors.

This IC is suitable for a camera use LED drive applications.

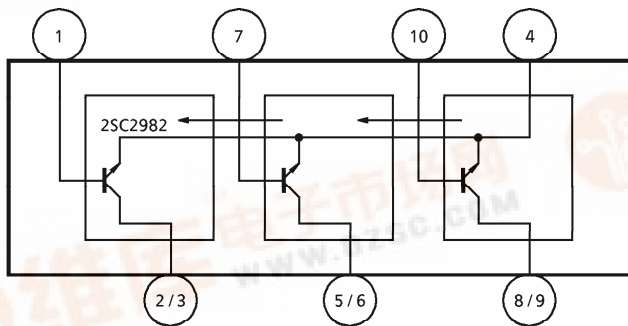
### FEATURES

- Suitable for LED drive circuit.
- Small package sealed : SSOP10
- Low saturation voltage
- 3-channel sink type

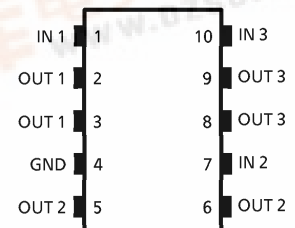


Weight : 0.10g (Typ.)

### BLOCK DIAGRAM



### PIN CONNECTION



980910EBA2

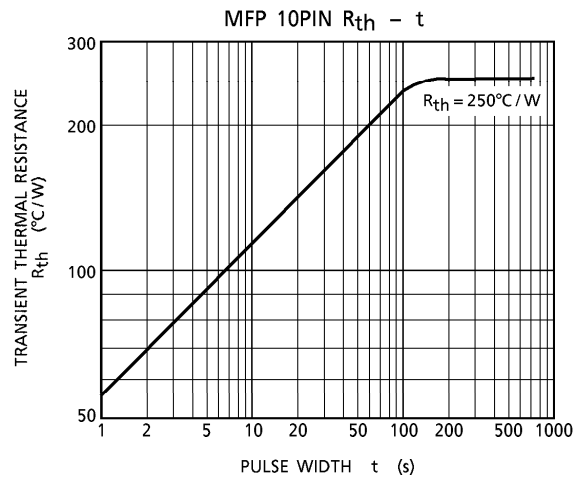
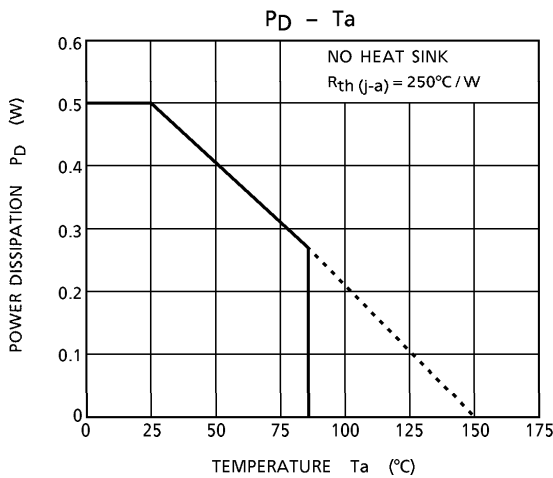
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**MAXIMUM RATINGS (Ta = 25°C)**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V <sub>CC</sub>	10	V
Breakdown Voltage	V <sub>CB0</sub>	10	V
	V <sub>CEO</sub>	10	V
	V <sub>EBO</sub>	6	V
Output Current	I <sub>O</sub>	2	A
	I <sub>O (peak)</sub>	(*) 4	
Base Current	I <sub>B</sub>	0.4	A
	I <sub>B (peak)</sub>	(*) 0.8	
Power Dissipation	P <sub>D</sub>	590	mW
Junction Temperature	T <sub>j</sub>	150	°C
Operating Temperature	T <sub>opr</sub>	-40~85	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C

(\*) T = 10ms Max. and maximum duty is less than 30%



**ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

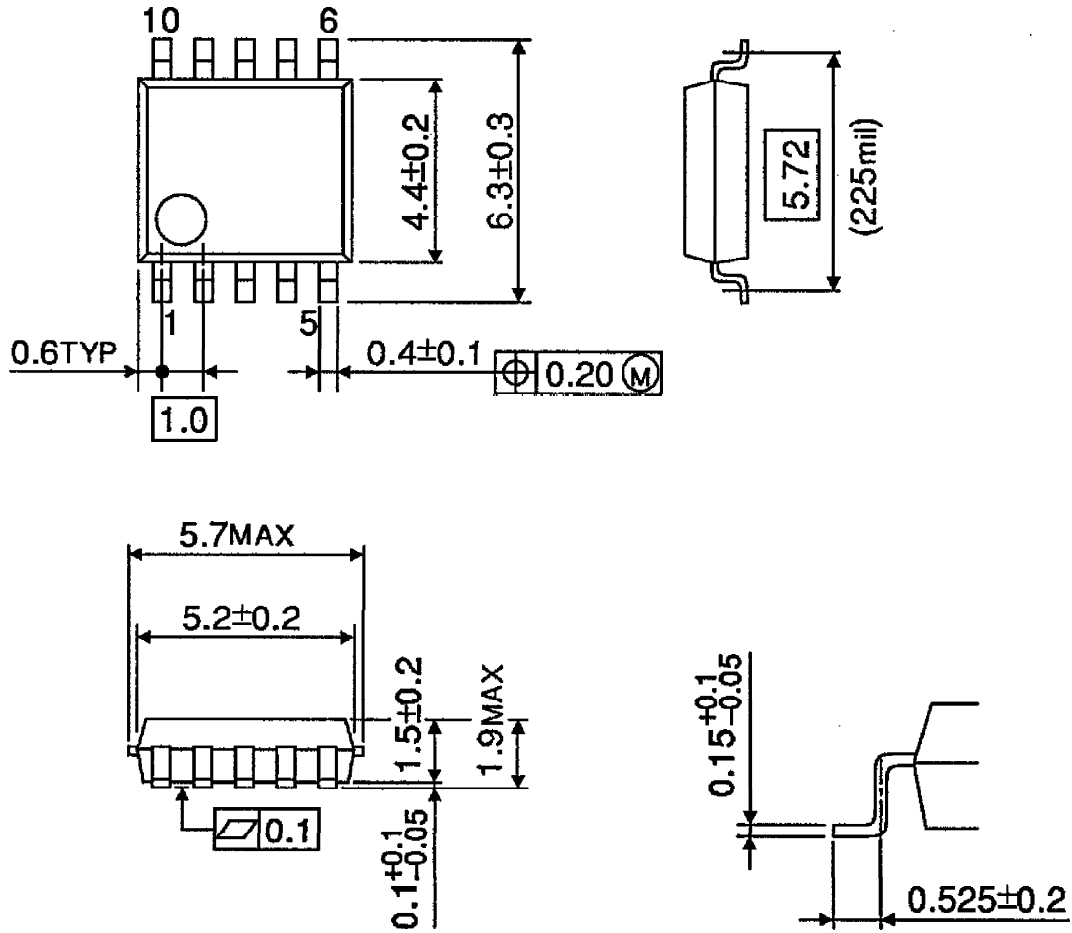
CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Gain	h <sub>FE (1)</sub>	—	V <sub>CE</sub> = 1V, I <sub>C</sub> = 0.5A	160	—	600	
	h <sub>FE (2)</sub>	—	V <sub>CE</sub> = 1V, I <sub>C</sub> = 2.0A	60	130	—	
Saturation Voltage	V <sub>CE (sat)</sub>	—	I <sub>C</sub> = 2A, I <sub>B</sub> = 50mA	—	—	0.5	V
Transition Frequency	f <sub>T</sub>	—	V <sub>CE</sub> = 2V, I <sub>C</sub> = 0.5A	—	150	—	MHz
Leakage Current	I <sub>OL</sub>	—	V <sub>CC</sub> = 10V	—	0	1.0	μA
Base-Emitter Forward Voltage	V <sub>BE</sub>	—	V <sub>CE</sub> = 1V, I <sub>C</sub> = 2.0A	—	0.84	1.5	V

980910EBA2'

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OUTLINE DRAWING  
SSOP10-P-225-1.00

Unit : mm



Weight : 0.10g (Typ.)